Lead-free Green
DMN2230U
N-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR
Please click here to visit our online spice models database.

## Features

- Low On-Resistance
- $\quad 110 \mathrm{~m} \Omega @ \mathrm{~V}_{\mathrm{GS}}=4.5 \mathrm{~V}$
- $145 \mathrm{~m} \Omega$ @ $\mathrm{V}_{\mathrm{GS}}=2.5 \mathrm{~V}$
- $\quad 230 \mathrm{~m} \Omega$ @ $\mathrm{V}_{\mathrm{Gs}}=1.8 \mathrm{~V}$
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Lead, Halogen and Antimony Free, RoHS Compliant
"Green" Device (Notes 2, 3 and 5)
- Qualified to AEC-Q101 Standards for High Reliability


TOP VIEW

## Mechanical Data

- Case: SOT-23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminal Connections: See Diagram
- Terminals: Finish - Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.008 grams (approximate)

DMN2230U

Electrical Characteristics
$@ T_{A}=25^{\circ} \mathrm{C}$ unless otherwise specified

| Characteristic | Symbol | Min | Typ | Max | Unit | Test Condition |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| OFF CHARACTERISTICS（Note 6） |  |  |  |  |  |  |
| Drain－Source Breakdown Voltage | BV ${ }_{\text {DSS }}$ | 20 | － | － | V | $\mathrm{V}_{\mathrm{GS}}=0 \mathrm{~V}, \mathrm{I}_{\mathrm{D}}=10 \mu \mathrm{~A}$ |
| Zero Gate Voltage Drain Current | IDSS | － | － | 1 | $\mu \mathrm{A}$ | $\mathrm{V}_{\mathrm{DS}}=20 \mathrm{~V}, \mathrm{~V}_{\mathrm{GS}}=0 \mathrm{~V}$ |
| Gate－Source Leakage | IGSS | － | － | $\pm 10$ | $\mu \mathrm{A}$ | $\mathrm{V}_{\mathrm{GS}}= \pm 12 \mathrm{~V}, \mathrm{~V}_{\mathrm{DS}}=0 \mathrm{~V}$ |
| ON CHARACTERISTICS（Note 6） |  |  |  |  |  |  |
| Gate Threshold Voltage | $\mathrm{V}_{\mathrm{GS}}$（th） | 0.5 | － | 1.0 | V | $\mathrm{V}_{\mathrm{DS}}=\mathrm{V}_{C S}, \mathrm{I}_{\mathrm{D}}=250 \mu \mathrm{~A}$ |
| Static Drain－Source On－Resistance | R DS（ON） | － | $\begin{gathered} 81 \\ 113 \\ 170 \end{gathered}$ | $\begin{aligned} & 110 \\ & 145 \\ & 230 \end{aligned}$ | $\mathrm{m} \Omega$ | $\mathrm{V}_{\mathrm{GS}}=4.5 \mathrm{~V}, \mathrm{I}_{\mathrm{D}}=2.5 \mathrm{~A}$ |
|  |  |  |  |  |  | $\mathrm{V}_{\mathrm{GS}}=2.5 \mathrm{~V}, \mathrm{I}_{\mathrm{D}}=1.5 \mathrm{~A}$ |
|  |  |  |  |  |  | $\mathrm{V}_{\mathrm{GS}}=1.8 \mathrm{~V}, \mathrm{I}_{\mathrm{D}}=1.0 \mathrm{~A}$ |
| Forward Transfer Admittance | $\left\|Y_{\text {fs }}\right\|$ | － | 5 | － | S | $\mathrm{V}_{\mathrm{DS}}=5 \mathrm{~V}, \mathrm{I}_{\mathrm{D}}=2.4 \mathrm{~A}$ |
| Diode Forward Voltage（Note 6） | $\mathrm{V}_{\text {SD }}$ | － | 0.8 | 1.1 | V | $\mathrm{V}_{\mathrm{GS}}=0 \mathrm{~V}, \mathrm{I}_{\mathrm{S}}=1.05 \mathrm{~A}$ |
| DYNAMIC CHARACTERISTICS |  |  |  |  |  |  |
| Input Capacitance | Ciss | － | 188 | － | pF | $\begin{aligned} & V_{D S}=10 \mathrm{~V}, V_{G S}=0 \mathrm{~V} \\ & f=1.0 \mathrm{MHz} \end{aligned}$ |
| Output Capacitance | $\mathrm{C}_{\text {oss }}$ | － | 44 | － | pF |  |
| Reverse Transfer Capacitance | Crss | － | 30 | － | pF |  |
| Turn－On Delay Time | $\mathrm{t}_{\mathrm{d}(\mathrm{on})}$ | － | 8 | － | ns | $\begin{aligned} & \mathrm{V}_{\mathrm{DD}}=10 \mathrm{~V}, \mathrm{R}_{\mathrm{L}}=10 \Omega \\ & \mathrm{I}_{\mathrm{D}}=1 \mathrm{~A}, \mathrm{~V}_{\mathrm{GEN}}=4.5 \mathrm{~V}, \mathrm{R}_{\mathrm{G}}=6 \Omega \end{aligned}$ |
| Rise Time | $\mathrm{tr}_{r}$ | － | 3.8 | － |  |  |
| Turn－Off Delay Time | $\mathrm{t}_{\mathrm{d} \text {（off）}}$ | － | 19.6 | － |  |  |
| Fall Time | $\mathrm{tf}_{f}$ | － | 8.3 | － |  |  |

Notes：6．Short duration pulse test used to minimize self－heating effect．


Fig． 1 Typical Output Characteristic


Fig． 2 Typical Transfer Characteristics

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Fig． 5 Gate Threshold Variation with Temperature


Fig． 7 Reverse Drain Current vs．Source－Drain Voltage


Fig． 4 Normalized Static Drain－Source On－Resistance vs．Ambient Temperature


Fig． 6 Typical Total Capacitance

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DMN2230U

## Ordering Information（Note 7）

Http：／／www． 100 y．com．tw

| Part Number | Case | Packaging |
| :---: | :---: | :---: |
| DMN2230U－7 | SOT－23 | 3000／Tape \＆Reel |

Notes：7．For packaging details，go to our website at http：／／www．diodes．com／datasheets／ap02007．pdf．

## Marking Information



## Package Outline Dimensions



| SOT－23 |  |  |  |
| :---: | :---: | :---: | :---: |
| Dim | Min | Max |  |
| A | 0.37 | 0.51 |  |
| B | 1.20 | 1.40 |  |
| C | 2.30 | 2.50 |  |
| D | 0.89 | 1.03 |  |
| E | 0.45 | 0.60 |  |
| G | 1.78 | 2.05 |  |
| H | 2.80 | 3.00 |  |
| $\mathbf{J}$ | 0.013 | 0.10 |  |
| K | 0.903 | 1.10 |  |
| L | 0.45 | 0.61 |  |
| $\mathbf{M}$ | 0.085 | 0.180 |  |
| $\boldsymbol{\alpha}$ | $0^{\circ}$ | $88^{\circ}$ |  |
| All Dimensions in $\mathbf{~ m m}$ |  |  |  |

## Suggested Pad Layout



| Dimensions | Value（in <br> $\mathbf{m m}$ ） |
| :---: | :---: |
| $\mathbf{Z}$ | 3.4 |
| $\mathbf{G}$ | 0.7 |
| $\mathbf{X}$ | 0.9 |
| $\mathbf{Y}$ | 1.4 |
| $\mathbf{C}$ | 2.0 |
| $\mathbf{E}$ | 0.9 |

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